

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L14	209	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L15	18	L14 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L16	218	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide) or cosi tisi nisi)	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L17	19	L16 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L18	33	L14 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L19	2	(w tungsten) with ((tungsten adj nitride) wn) with (anneal\$ with (hydrogen "h.sub.2") with (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L20	2	L19 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/12/05 20:38
L21	218	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide) or cosi tisi nisi)	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L22	19	L21 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L23	209	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L24	33	L23 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:38
L25	52	L15 or L17 or L18 or L20 or L22 or L24	US-PGPUB; USPAT	OR	ON	2005/12/05 20:38
L26	37	L25 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/12/05 20:38

L27	4	26 and (anneal\$ with (hydrogen "h. sub.2") with (nitrogen "n.sub.2"))	US-PGPUB; USPAT	OR	OFF	2005/12/05 20:39
S1	38	(HO-TZU-EN CHANG-CHIH-HAO WU-CHANG-RONG SU-KUO-HUI).in.	US-PGPUB; USPAT	OR	OFF	2005/02/02 21:06
S2	372	nanya.asn.	US-PGPUB; USPAT	OR	OFF	2005/02/02 19:03
S3	26	S2 and (stack\$ with (gate transistor fet mosfet))	US-PGPUB; USPAT	OR	OFF	2005/02/02 21:07
S4	151	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/02/03 14:10
S5	15	S4 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S6	155	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide) or cosi tisi nisi)	US-PGPUB; USPAT	OR	OFF	2005/02/02 18:27
S7	16	S6 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S8	1	S7 not S5	US-PGPUB; USPAT	OR	OFF	2005/02/02 18:27
S9	23	S4 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub. 2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S10	22	S9 not S7	US-PGPUB; USPAT	OR	OFF	2005/02/02 18:29
S11	94	(anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")) with (gate transistor))	US-PGPUB; USPAT	OR	ON	2005/02/02 21:10
S12	84	S11 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/02/03 13:51
S13	2	(w tungsten) with ((tungsten adj nitride) wn) with (anneal\$ with (hydrogen "h.sub.2") with (nitrogen "n.sub.2"))	US-PGPUB; USPAT	OR	OFF	2005/02/02 21:07
S14	2	S13 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/12/05 17:11
S15	1	S2 and (anneal\$ with (hydrogen "h. sub.2") with (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/02/02 21:09
S16	1	S2 and (anneal\$ with (hydrogen "h. sub.2") with (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	ON	2005/02/02 21:09
S17	1	S2 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub. 2"))))	US-PGPUB; USPAT	OR	ON	2005/02/02 21:09

S18	98	(anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")))) with (gate transistor fet mosfet nfet pfet pmosfet nmosfet nmos pmos)	US-PGPUB; USPAT	OR	ON	2005/02/02 21:11
S19	4	S18 not S11	US-PGPUB; USPAT	OR	ON	2005/02/02 21:11
S20	4	S19 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/02/02 21:11
S21	19	(US-20010002273-\$ or US-20010015430-\$ or US-20020058410-\$ or US-20020094643-\$ or US-20020171146-\$ or US-20020190294-\$ or US-20030134460-\$ or US-20040238876-\$).did. or (US-5182624-\$ or US-5235195-\$ or US-5273910-\$ or US-5341016-\$ or US-5633200-\$ or US-5789312-\$ or US-5923999-\$ or US-6091122-\$ or US-6114736-\$ or US-6284634-\$ or US-6322849-\$).did.	US-PGPUB; USPAT	OR	OFF	2005/02/03 13:28
S22	13	S21 and (anneal\$ with ((hydrogen "h.sub.2" "h2") and (nitrogen "n. sub.2" "n2")))	US-PGPUB; USPAT	OR	OFF	2005/02/03 14:11
S23	2	S22 and (wn (tungsten adj nitride))	US-PGPUB; USPAT	OR	OFF	2005/02/03 13:48
S24	19	S21 and (anneal\$)	US-PGPUB; USPAT	OR	OFF	2005/02/03 13:46
S25	41	((forming adj gas adj anneal\$) fga) with ((hydrogen "h.sub.2" "h2") and (nitrogen "n.sub.2" "n2"))	US-PGPUB; USPAT	OR	OFF	2005/02/03 13:51
S26	6	S25 and (wn (tungsten adj nitride))	US-PGPUB; USPAT	OR	OFF	2005/02/03 13:48
S27	35	S25 not S26	US-PGPUB; USPAT	OR	OFF	2005/02/03 13:51
S28	35	S27 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/02/03 14:05
S29	2649	(tungsten adj silicide) with ((cobalt nickel titanium) adj silicide)	US-PGPUB; USPAT	OR	ON	2005/02/03 14:04
S30	467	((tungsten adj silicide) with ((cobalt nickel titanium) adj silicide) with (gate transistor fet mosfet))	US-PGPUB; USPAT	OR	ON	2005/02/03 14:05
S31	438	S30 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/02/03 16:46
S32	396	((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/02/03 14:32
S33	33	S32 and (anneal\$ with ((hydrogen "h.sub.2" "h2") and (nitrogen "n. sub.2" "n2")))	US-PGPUB; USPAT	OR	OFF	2005/02/03 14:45

S34	29	S33 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/02/03 14:11
S35	1300	((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn))	US-PGPUB; USPAT	OR	OFF	2005/02/03 14:32
S36	78	S35 and (anneal\$ with ((hydrogen "h.sub.2" "h2") and (nitrogen "n. sub.2" "n2")))	US-PGPUB; USPAT	OR	OFF	2005/02/03 14:45
S37	73	S36 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/02/03 19:39
S38	44	S37 not S34	US-PGPUB; USPAT	OR	ON	2005/02/03 14:46
S39	1	10/051981	US-PGPUB; USPAT	OR	ON	2005/02/03 17:39
S40	0	"10745114"	US-PGPUB; USPAT	OR	ON	2005/02/03 18:26
S41	1	"10/745114"	US-PGPUB; USPAT	OR	ON	2005/02/03 18:26
S42	2	"09/745114"	US-PGPUB; USPAT	OR	ON	2005/02/03 19:38
S43	178	gate with clean with (HF or hydrofluoric)	US-PGPUB; USPAT	OR	ON	2005/02/03 19:40
S44	168	S43 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/02/03 19:41
S45	28	gate with clean with (HF or hydrofluoric) with polysilicon	US-PGPUB; USPAT	OR	ON	2005/02/03 19:40
S46	27	S45 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 15:26
S47	214	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide) or cosi tisi nisi)	US-PGPUB; USPAT	OR	OFF	2005/10/07 15:23
S48	19	S47 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:11
S49	205	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/10/07 15:23
S50	32	S49 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:12

S51	480	((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/10/07 15:25
S52	47	S51 and (anneal\$ with ((hydrogen "h.sub.2" "h2") and (nitrogen "n. sub.2" "n2")))	US-PGPUB; USPAT	OR	OFF	2005/10/07 15:25
S53	34	S52 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 16:07
S54	517	(cap capping) with (anneal annealing annealed) with (before after)	US-PGPUB; USPAT	OR	ON	2005/10/07 15:30
S55	191	S54 and gate and (w tungsten)	US-PGPUB; USPAT	OR	ON	2005/10/07 15:30
S56	164	S55 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 15:30
S57	56	(cap capping) with (anneal annealing annealed) with (before and after)	US-PGPUB; USPAT	OR	ON	2005/10/07 17:17
S58	51	S57 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 16:35
S59	13	S58 and (transistor mosfet fet gate) and (w tungsten)	US-PGPUB; USPAT	OR	ON	2005/10/07 15:30
S60	13	S48 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 16:39
S61	1	("20020127888").PN.	US-PGPUB; USPAT	OR	OFF	2005/10/07 16:07
S62	0	(gate near2 (cap capping)) with (anneal annealing annealed) with (before and after)	US-PGPUB; USPAT	OR	ON	2005/10/07 16:35
S63	6	(gate near2 (cap capping)) same ((anneal annealing annealed) with (before and after))	US-PGPUB; USPAT	OR	ON	2005/10/07 16:35
S64	15	(gate near2 (cap capping)) same ((anneal annealing annealed) with (before after))	US-PGPUB; USPAT	OR	ON	2005/10/07 17:27
S65	6	S63 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 17:28
S66	11	S64 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 16:36
S67	5	S66 not S65	US-PGPUB; USPAT	OR	ON	2005/10/07 16:37
S68	141	S49 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 16:39
S69	32	S50 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/10/07 16:40
S70	105	(gate near2 (cap capping)) same (anneal annealing annealed)	US-PGPUB; USPAT	OR	ON	2005/10/07 18:36

S71	83	S70 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/10/07 17:28
S72	7	(gate near2 (cap capping)) same (after near2 (anneal annealing annealed))	US-PGPUB; USPAT	OR	ON	2005/10/07 18:37
S73	0	(dual near2 (cap capping)) same (after near2 (anneal annealing annealed))	US-PGPUB; USPAT	OR	ON	2005/12/05 17:12
S74	2	(dual near2 (cap capping)) same ((anneal annealing annealed))	US-PGPUB; USPAT	OR	ON	2005/10/07 18:37
S75	209	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S76	18	S75 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S77	218	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide) or cosi tisi nisi)	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S78	19	S77 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S79	33	S75 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:10
S80	2	(w tungsten) with ((tungsten adj nitride) wn) with (anneal\$ with (hydrogen "h.sub.2") with (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:11
S81	2	S80 not (@ad>"20031010" or @rlad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/12/05 17:13
S82	218	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide) or cosi tisi nisi)	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:11
S83	19	S82 and (anneal\$ with (wn (tungsten adj nitride)))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:11
S84	209	(stack\$ with (gate transistor fet mosfet)) and ((gate transistor fet mosfet) with (tungsten w)) and ((gate transistor fet mosfet) with ((tungsten adj nitride) wn)) and ((cobalt titanium nickel) adj (polycide silicide polysilicide))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:12

S85	33	S84 and (anneal\$ with ((hydrogen "h.sub.2") and (nitrogen "n.sub.2")))	US-PGPUB; USPAT	OR	OFF	2005/12/05 17:12
S86	52	S76 or S78 or S79 or S81 or S83 or S85	US-PGPUB; USPAT	OR	ON	2005/12/05 17:13
S87	37	S86 not (@ad>"20031010" or @lad>"20031010")	US-PGPUB; USPAT	OR	ON	2005/12/05 18:04